

isc Silicon NPN Power Transistor

2SC937

DESCRIPTION

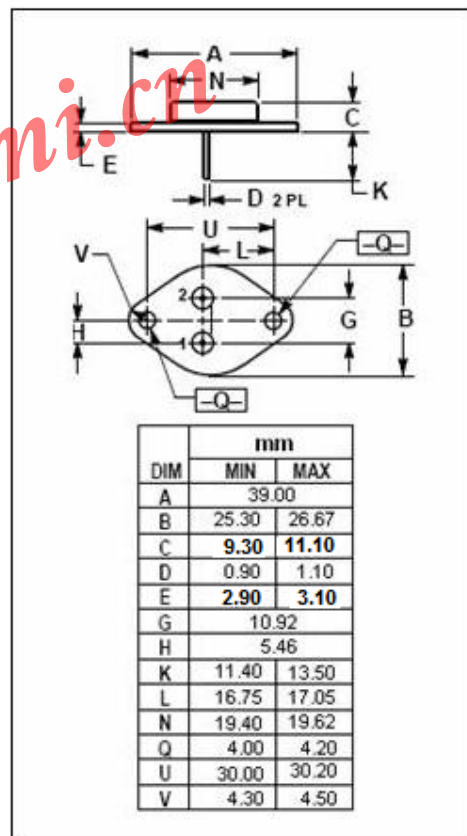
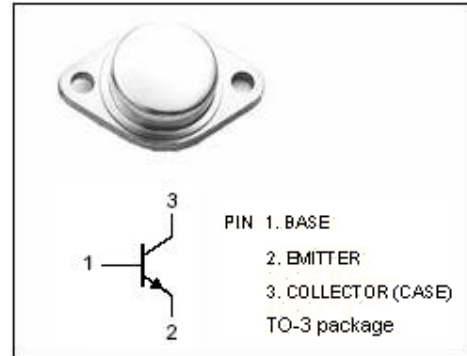
- High Breakdown Voltage-
: $V_{CBO}=1200V(\text{Min})$
- High Reliability

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	2.5	A
I_{CP}	Collector Current-Pulse	6	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	22	W
T_J	Junction Temperature	125	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-45~125	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC937****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; R_{BE}=\infty$	500			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			1.8	V
I_{CBX}	Collector Cutoff Current	$V_{CB}=1200\text{V}; V_{EB}=1.5\text{V}$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			0.2	mA
t_f	Fall Time	$I_C=2.5\text{A}, I_{B1}=0.8\text{A}, I_{B2}=-1.1\text{A}; L_B=10\mu\text{H}$			1.2	μs

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